

TECHNICAL DATA
 DATA SHEET 1153, REV. -

HERMETIC POWER SCHOTTKY RECTIFIER

Low Reverse Leakage

200°C Operating Temperature

Applications:

· Switching Power Supply · Converters · Free-Wheeling Diodes · Polarity Protection Diode ·

Features:

- Low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Available with Ceramic Seals

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	45	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave	200	A
Max. Junction Temperature	T_J	-	-65 to +200	°C
Max. Storage Temperature	T_{stg}	-	-65 to +175	°C
Max. Thermal Resistance	$R_{\theta JC}$	Single	0.60	°C/W
Max. Thermal Resistance	$R_{\theta JC}$	Common Cathode, Common Anode, Doubler	0.30	°C/W

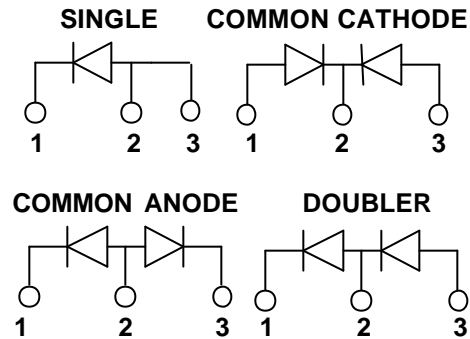
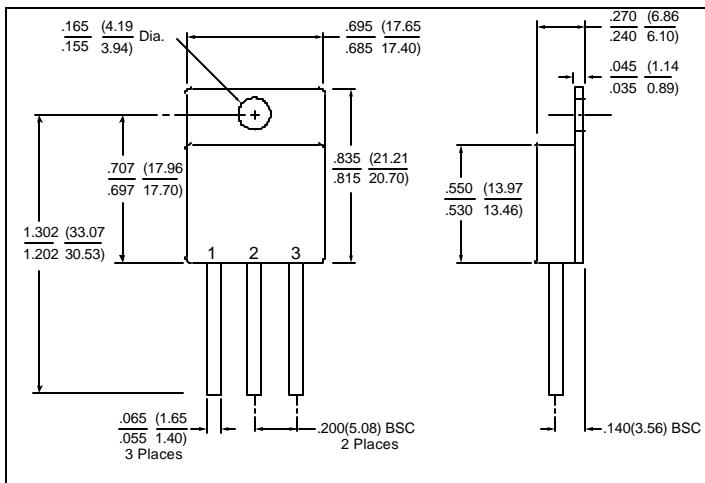
Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 45A, Pulse, $T_J = 25^\circ\text{C}$	1.10	V
	V_{F2}	@ 45A, Pulse, $T_J = 125^\circ\text{C}$	0.92	V
Max. Reverse Current	I_{R1}	@ $V_R = 100\text{V}$, Pulse, $T_J = 25^\circ\text{C}$	0.30	mA
	I_{R2}	@ $V_R = 100\text{V}$, Pulse, $T_J = 125^\circ\text{C}$	3.0	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$, $V_{SIG} = 50\text{mV}$ (p-p)	1500	pF

SENSITRON

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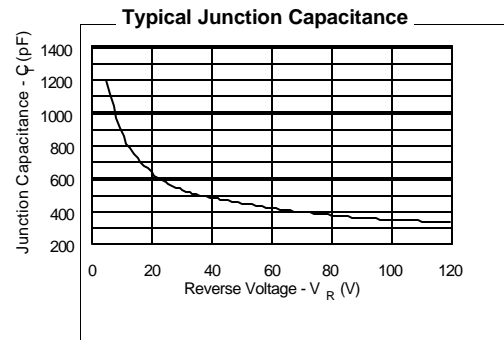
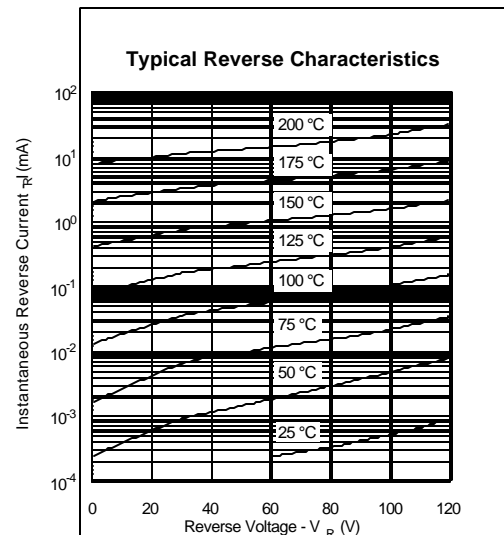
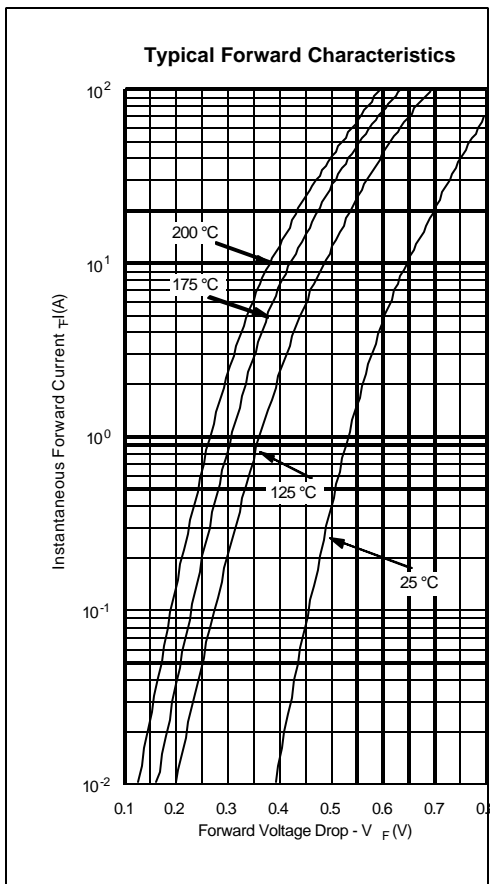
MECHANICAL DIMENSIONS: In Inches / mm



TO-258

PINOUT TABLE

TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
DUAL RECTIFIER, COMMON CATHODE (P)	ANODE 1	COMMON CATHODE	ANODE 2
DUAL RECTIFIER, COMMON ANODE (N)	CATHODE 1	COMMON ANODE	CATHODE 2
DOUBLER (D)	CATHODE	ANODE/CATHODE	ANODE



Curves are given for un-packaged die.

TECHNICAL DATA

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